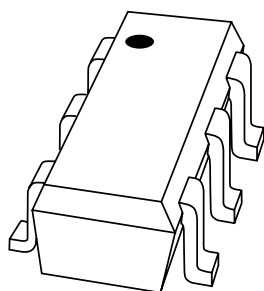


DATA SHEET



PUMD12

NPN/PNP resistor-equipped
transistor

Product specification

1999 Apr 26

NPN/PNP resistor-equipped transistor

PUMD12

FEATURES

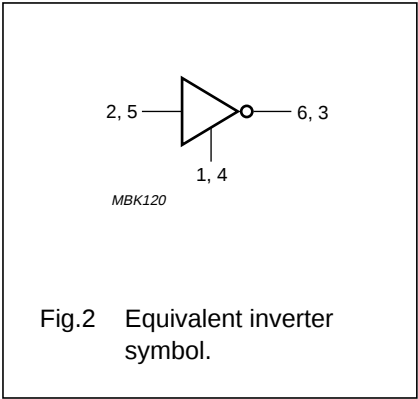
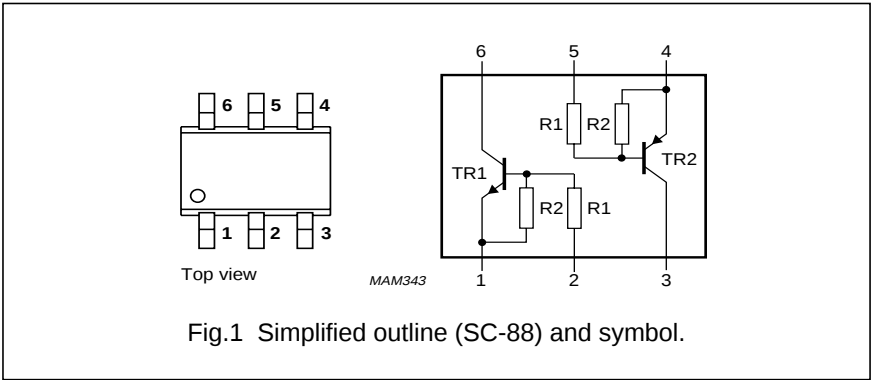
- Transistors with different polarity and built-in bias resistors R1 and R2 (typ. 47 kΩ each)
- No mutual interference between the transistors
- Simplification of circuit design
- Reduces number of components and board space.

APPLICATIONS

- Especially suitable for space reduction in interface and driver circuits
- Inverter circuit configurations without use of external resistors.

DESCRIPTION

NPN/PNP resistor-equipped transistors in an SC-88 plastic package.



PINNING

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
6, 3	collector TR1; TR2

MARKING

TYPE NUMBER	MARKING CODE
PUMD12	Dt1

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor; for the PNP transistor with negative polarity					
V _{CBO}	collector-base voltage	open emitter	–	50	V
V _{CEO}	collector-emitter voltage	open base	–	50	V
V _{EBO}	emitter-base voltage	open collector	–	10	V
V _I	input voltage positive negative		–	+40	V
			–	–10	V
I _O	output current (DC)		–	100	mA
I _{CM}	peak collector current		–	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	200	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	–	300	mW

Note

1. Refer to SC-88 standard mounting conditions.

NPN/PNP resistor-equipped transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	416	K/W

Note

1. Refer to SC-88 standard mounting conditions.

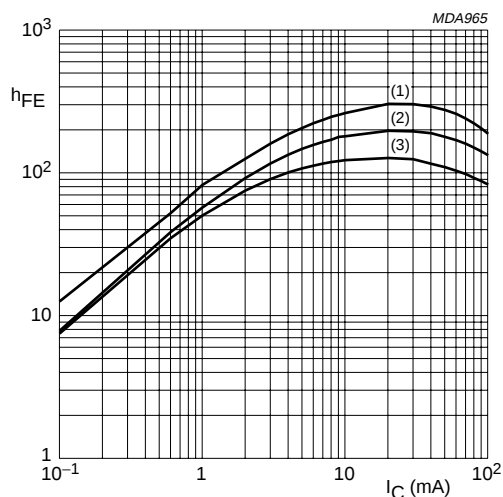
CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transistor; for the PNP transistor with negative polarity						
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 50\text{ V}$	–	–	100	nA
I_{CEO}	collector cut-off current	$I_B = 0; V_{CE} = 30\text{ V}$	–	–	1	μA
		$I_B = 0; V_{CE} = 30\text{ V}; T_j = 150\text{ °C}$	–	–	50	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	90	μA
h_{FE}	DC current gain	$I_C = 5\text{ mA}; V_{CE} = 5\text{ V}$	80	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	–	150	mV
$V_{i(off)}$	input-off voltage	$I_C = 100\text{ }\mu\text{A}; V_{CE} = 5\text{ V}$	–	1.2	0.8	V
$V_{i(on)}$	input-on voltage	$I_C = 2\text{ mA}; V_{CE} = 0.3\text{ V}$	3	1.6	–	V
R_1	input resistor		33	47	61	k Ω
$\frac{R_2}{R_1}$	resistor ratio		0.8	1	1.2	
C_c	collector capacitance	$I_E = I_E = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$				
	TR1		–	–	2.5	pF
	TR2		–	–	3	pF

NPN/PNP resistor-equipped transistor

PUMD12



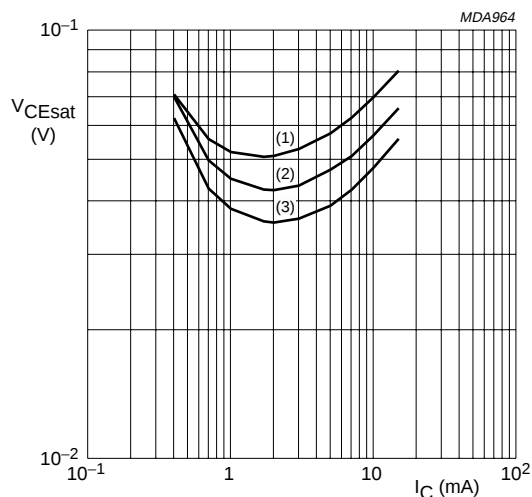
TR1 (NPN); $V_{CE} = 5 \text{ V}$.

(1) $T_{amb} = 150 \text{ }^{\circ}\text{C}$.

(2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.

(3) $T_{amb} = -40 \text{ }^{\circ}\text{C}$.

Fig.3 DC current gain as a function of collector current; typical values.



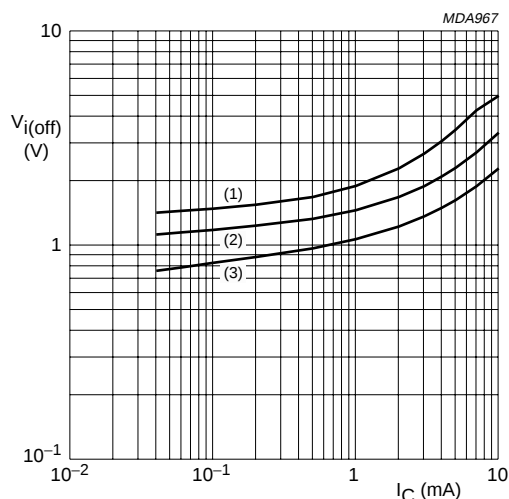
TR1 (NPN); $I_C/I_B = 20$.

(1) $T_{amb} = 100 \text{ }^{\circ}\text{C}$.

(2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.

(3) $T_{amb} = -40 \text{ }^{\circ}\text{C}$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



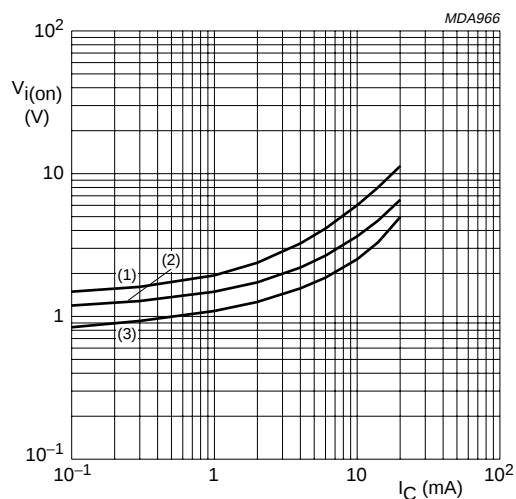
TR1 (NPN); $V_{CE} = 5 \text{ V}$.

(1) $T_{amb} = -40 \text{ }^{\circ}\text{C}$.

(2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.

(3) $T_{amb} = 100 \text{ }^{\circ}\text{C}$.

Fig.5 Input-off voltage as a function of collector current; typical values.



TR1 (NPN); $V_{CE} = 0.3 \text{ V}$.

(1) $T_{amb} = -40 \text{ }^{\circ}\text{C}$.

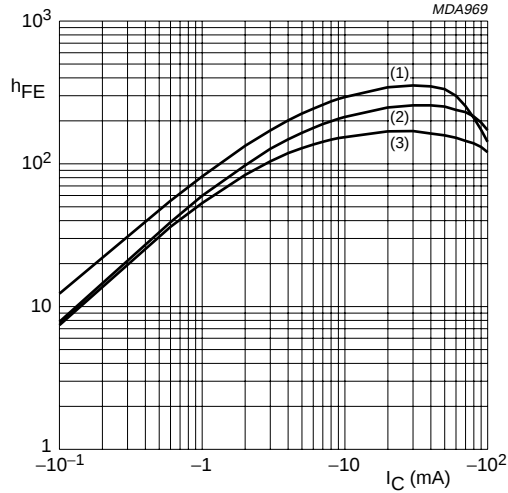
(2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.

(3) $T_{amb} = 100 \text{ }^{\circ}\text{C}$.

Fig.6 Input-on voltage as a function of collector current; typical values.

NPN/PNP resistor-equipped transistor

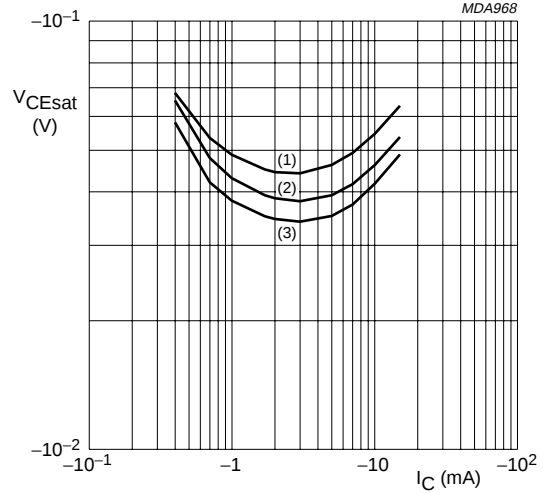
PUMD12



TR2 (PNP); $V_{CE} = -5$ V.

- (1) $T_{amb} = 150$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = -40$ °C.

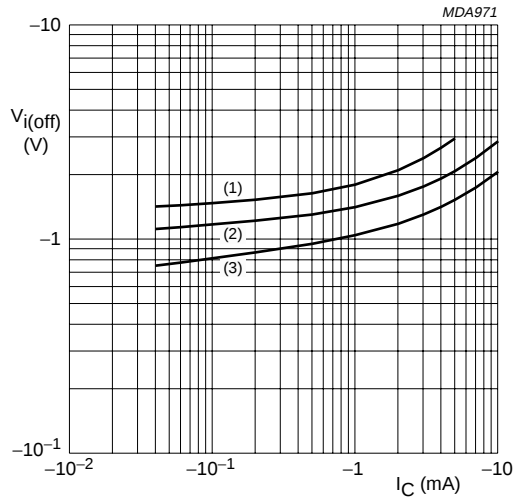
Fig.7 DC current gain as a function of collector current; typical values.



TR2 (PNP); $I_C/I_B = 20$.

- (1) $T_{amb} = 100$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = -40$ °C.

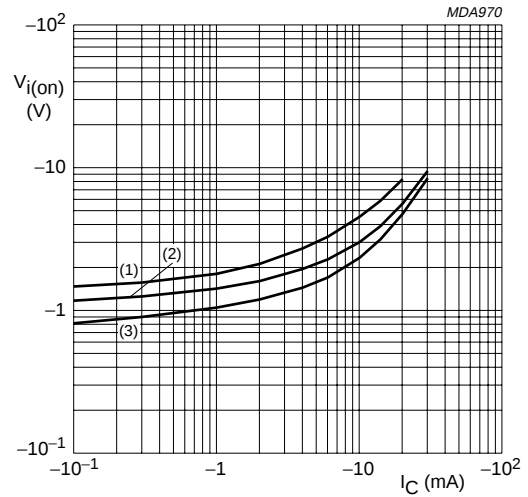
Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



TR2 (PNP); $V_{CE} = -5$ V.

- (1) $T_{amb} = -40$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = 100$ °C.

Fig.9 Input-off voltage as a function of collector current; typical values.



TR2 (PNP); $V_{CE} = -0.3$ V.

- (1) $T_{amb} = -40$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = 100$ °C.

Fig.10 Input-on voltage as a function of collector current; typical values.

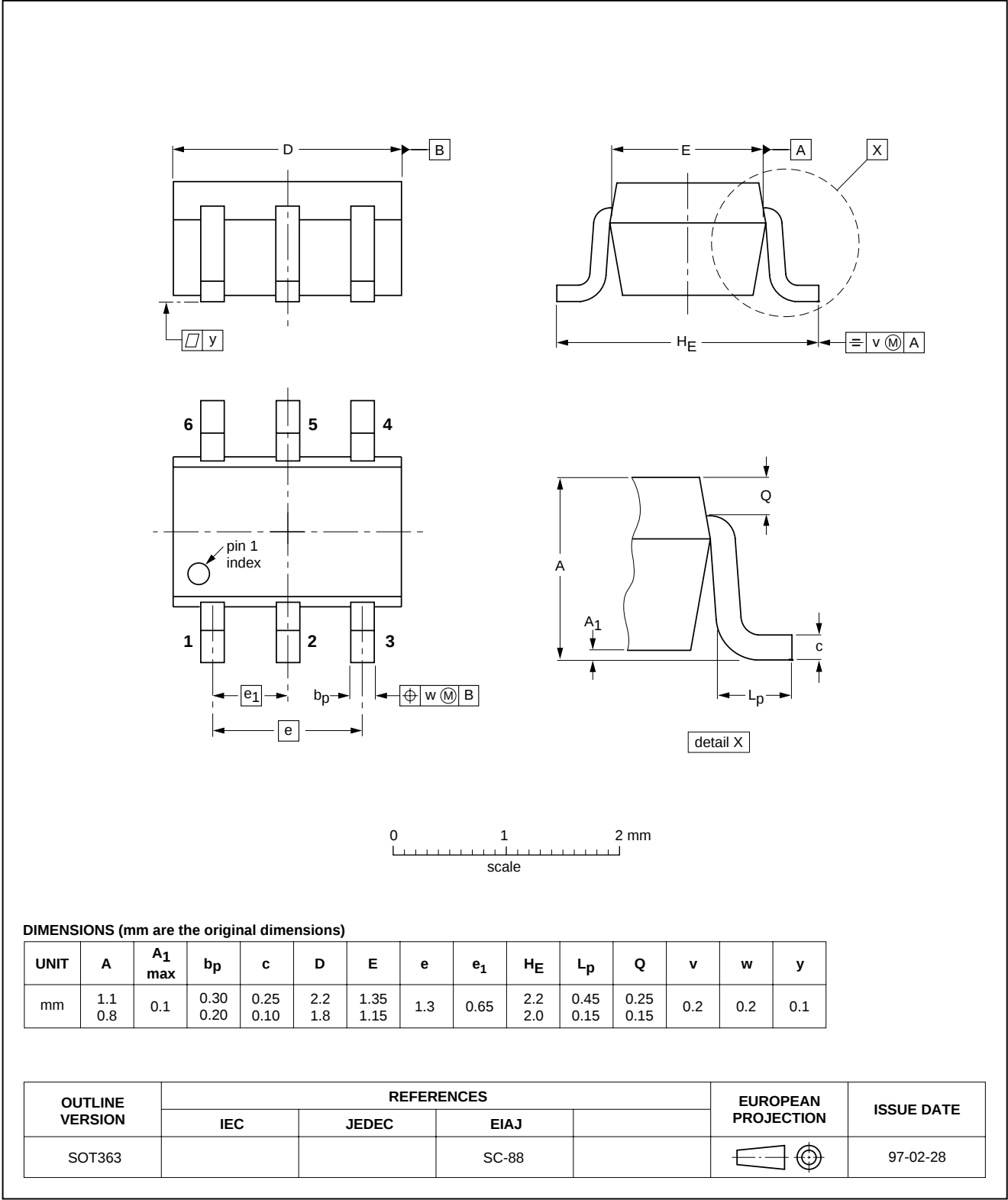
NPN/PNP resistor-equipped transistor

PUMD12

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT363



NPN/PNP resistor-equipped transistor

PUMD12

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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